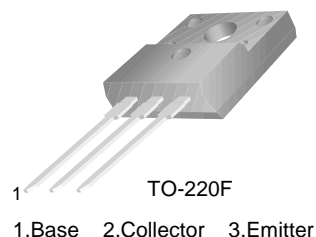


## KSC5367F

KSC5367F

### High Voltage and High Reliability

- High speed Switching
- Wide Safe Operating Area
- High Collector-Base Voltage



### NPN Triple Diffused Planar Silicon Transistor

#### Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	1600	V
$V_{CEO}$	Collector-Emitter Voltage	800	V
$V_{EBO}$	Emitter-Base Voltage	12	V
$I_C$	Collector Current (DC)	3	A
$I_{CP}$	*Collector Curren (Pulse)	6	A
$I_B$	Base Current (DC)	2	A
$I_{BP}$	*Base Current (Pulse)	4	A
$P_C$	Power Dissipation( $T_C=25^\circ\text{C}$ )	40	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature	- 65 ~ 150	$^\circ\text{C}$

\* Pulse Test: Pulse Width=5ms, Duty Cycle $\leq$ 10%

#### Thermal Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Characteristics		Rating	Unit
$R_{\theta jc}$	Thermal Resistance	Junction to Case	3.1	$^\circ\text{C/W}$
$R_{\theta ja}$		Junction to Ambient	62.5	

**Electrical Characteristics**  $T_C=25^{\circ}\text{C}$  unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$BV_{CBO}$	Collector-Base Breakdown Voltage	$I_C = 0.5\text{mA}, I_E = 0$	1600	-	-	V
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 5\text{mA}, I_B = 0$	800	-	-	V
$BV_{EBO}$	Emitter-Base Breakdown Voltage	$I_C = 0.5\text{mA}, I_C = 0$	12	-	-	V
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = 1,600\text{V}, I_E = 0$	-	-	20	$\mu\text{A}$
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = 12\text{V}, I_C = 0$	-	-	20	$\mu\text{A}$
$h_{FE1}$ $h_{FE2}$	DC Current Gain	$V_{CE} = 3\text{V}, I_C = 0.4\text{A}$ $V_{CE} = 10\text{V}, I_C = 5\text{mA}$	12 8	- -	35 -	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 250\text{mA}, I_B = 25\text{mA}$	-	-	2.5	V
		$I_C = 500\text{mA}, I_B = 50\text{mA}$	-	-	4.0	V
		$I_C = 1\text{A}, I_B = 0.2\text{A}$	-	-	2.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 500\text{mA}, I_B = 50\text{mA}$	-	-	1.5	V
$C_{ob}$	Output Capacitance	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$	-	40	-	pF
$t_{ON}$	Turn ON Time	$V_{CC} = 125\text{V}, I_C = 0.5\text{A}$	-	-	0.5	$\mu\text{s}$
$t_{STG}$	Storage Time	$I_{B1} = 42\text{mA}, I_{B2} = -333\text{mA}$	-	-	2.2	$\mu\text{s}$
$t_F$	Falling Time	$R_L = 250\Omega$	-	-	0.5	$\mu\text{s}$
$t_{ON}$	Turn ON Time	$V_{CC} = 250\text{V}, I_C = 1\text{A}$	-	-	0.5	$\mu\text{s}$
$t_{STG}$	Storage Time	$I_{B1} = 0.2\text{A}, I_{B2} = -0.4\text{A}$	-	-	4.0	$\mu\text{s}$
$t_F$	Falling Time	$R_L = 250\Omega$	-	-	0.5	$\mu\text{s}$

# Typical Characteristics

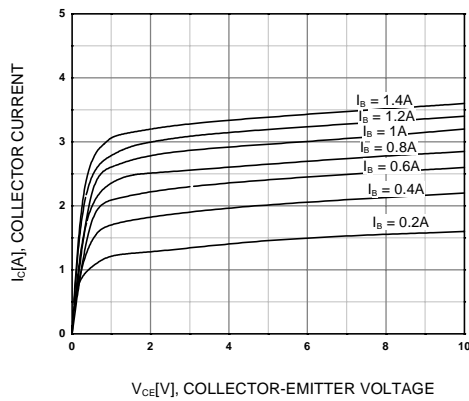


Figure 1. Static Characteristic

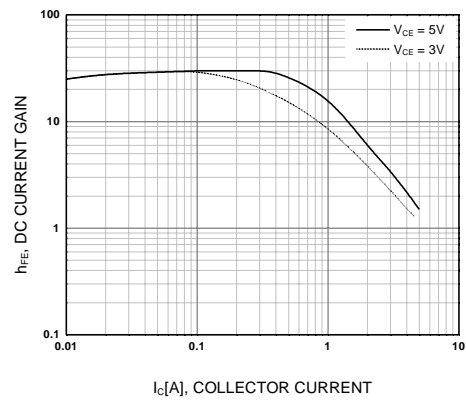


Figure 2. DC current Gain

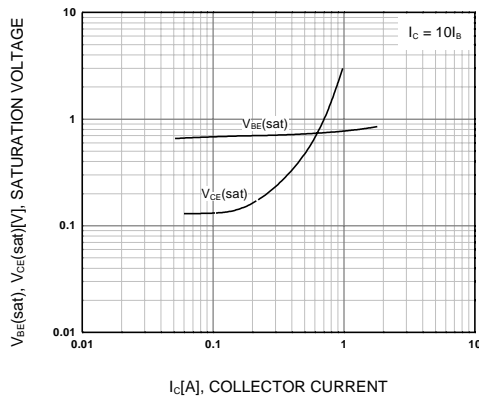


Figure 3. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

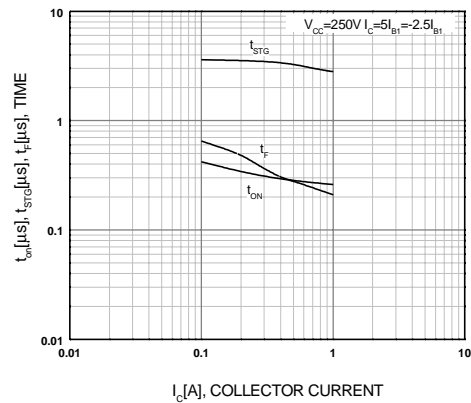


Figure 4. Switching Time

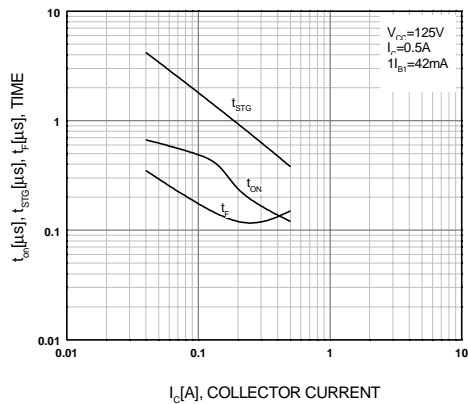


Figure 5. Switching Time

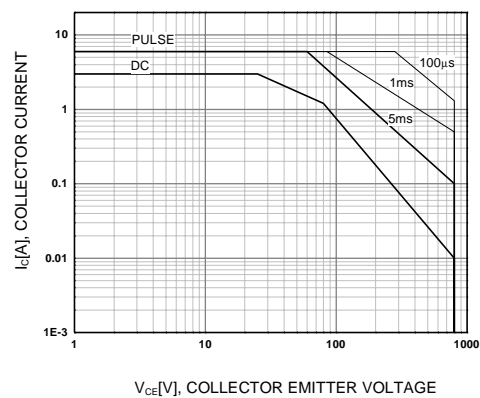


Figure 6. Safe Operating Area

## Typical Characteristics (Continued)

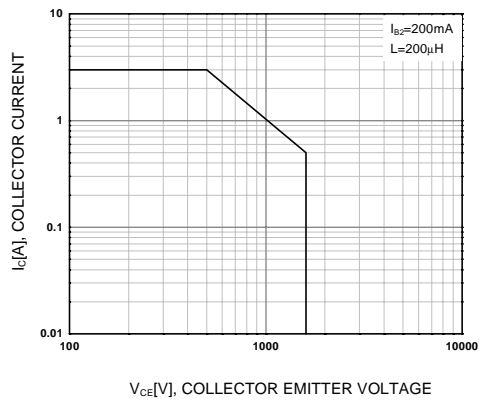


Figure 7. Reverse Bias Safe Operating Area

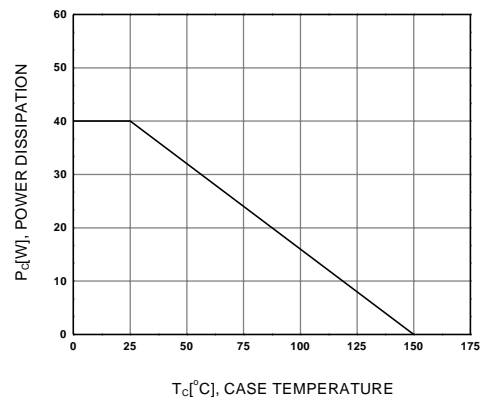
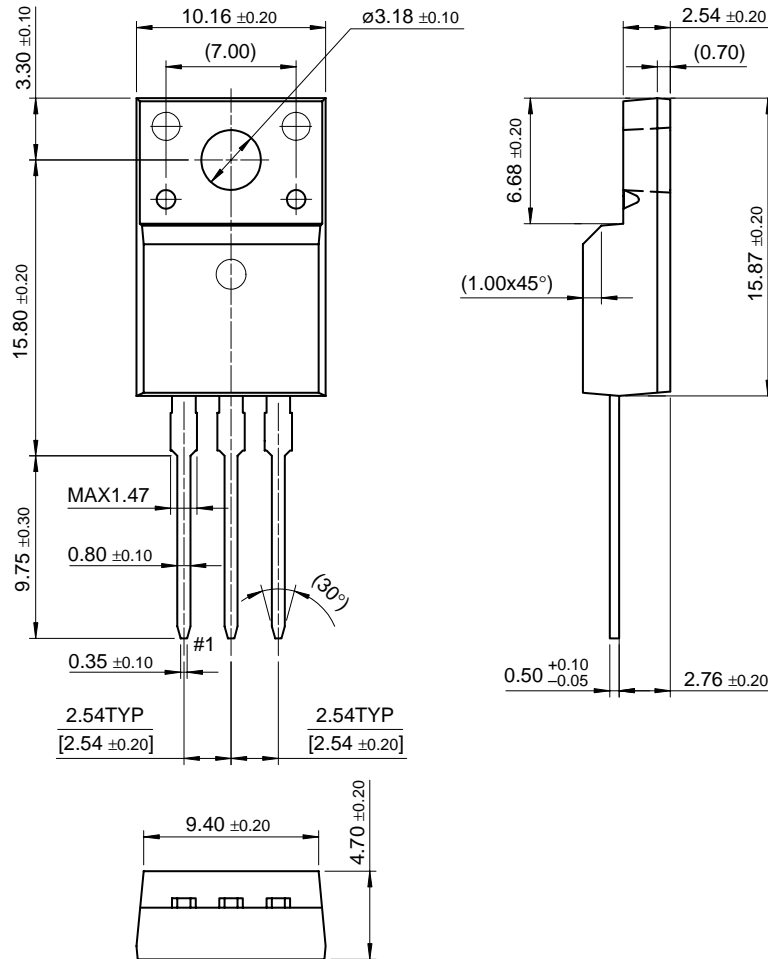


Figure 8. Power Derating

# Package Dimensions

## TO-220F



Dimensions in Millimeters

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